WHAT IS CLAIMED IS:

1. A method for manufacturing a semiconductor laser device, comprising the steps of:

(a) sequentially forming a first conductive-type clad layer, an active layer, and a second conductive-type clad layer, on a first conductive-type semiconductor substrate;

(b) forming a ridge structure by selectively etching the second conductive-type clad layer;

(c) forming a current blocking layer around the ridge structure, said current blocking layer having protrusions on the upper surface thereof adjacent to the ridge structure, and an amorphous and/or polycrystalline layer on a partial area thereof;

(d) wet-etching the upper surface of the current blocking layer, so that at least the amorphous and/or polycrystalline layer is removed from the current blocking layer and the protrusions are reduced in size; and

(e) forming a second conductive-type contact layer on the upper surface of the current blocking layer.

2. The method as set forth in claim 1,

wherein an upper surface of the second conductive-type clad layer is a {100} plane, and an inclined surface of the

ridge structure of the second conductive-type clad layer is near to a {111} plane.

3. The method as set forth in claim 1;

wherein the step (b) includes:

(b-1) forming a mask at a partial are of an upper surface of the second conductive-type clad layer; and

(b-2) etching the second conductive-type clad layer so that the ridge structure is formed at the area of the mask.

4. The method as set forth in claim 3,

wherein the step (d) includes the step of wet-etching the upper surface of the current blocking layer after the mask is removed.

5. The method as set forth in claim 1,

wherein the current blocking layer is made of a first conductive-type AlGaAs/GaAs material.

6. The method as set forth in claim 5,

wherein the step (d) includes the step of wet-etching the upper surface of the current blocking layer using an EG-group etchant.